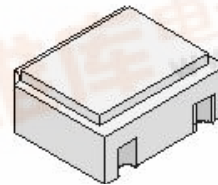




Data Sheet No. 2N4957UB

Type 2N4957UB**Geometry 0006****Polarity PNP****Qual Level: JAN - JANTXV****Generic Part Number:
2N4957UB****REF: MIL-PRF-19500/426****Features:**[Request Quotation](#)

- Small signal RF silicon transistor designed for high-gain, low-noise applications.
- Housed in a [cersot](#) case.
- Also available in chip form using the [0006](#) chip geometry.
- The Min and Max limits shown are per [MIL-PRF-19500/426](#) which Semicoa meets in all cases.



Cersot

Maximum Ratings $T_C = 25^{\circ}\text{C}$ unless otherwise specified

Rating	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	30	V
Collector-Base Voltage	V_{CBO}	30	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current, Continuous	I_C	30	A
Operating Junction Temperature	T_J	-65 to +200	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-65 to +200	$^{\circ}\text{C}$

Electrical Characteristics

 $T_C = 25^{\circ}\text{C}$ unless otherwise specified

OFF Characteristics	Symbol	Min	Max	Unit
Collector-Base Breakdown Voltage $I_C = 100\ \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	30	---	V
Collector-Emitter Breakdown Voltage $I_C = 1.0\ \text{mA}, I_B = 0$	$V_{(BR)CEO}$	30	---	V
Emitter-Base Breakdown Voltage $I_E = 100\ \mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	3.0	---	V
Collector-Base Cutoff Current $V_{CB} = 20\ \text{V}, I_E = 0, T_C = +25^{\circ}\text{C}$	I_{CBO1}	---	100	na
Collector-Base Cutoff Current $V_{CB} = 20\ \text{V}, I_E = 0, T_C = +150^{\circ}\text{C}$	I_{CBO2}	---	100	μA

ON Characteristics	Symbol	Min	Max	Unit
DC Current Gain				
$I_C = 0.5\ \text{mA}, V_{CE} = 10\ \text{V}$	h_{FE1}	15	---	---
$I_C = 2.0\ \text{mA}, V_{CE} = 10\ \text{V}$	h_{FE2}	20	---	---
$I_C = 5.0\ \text{mA}, V_{CE} = 10\ \text{V}$	h_{FE3}	30	165	---
$I_C = 5.0\ \text{mA}, V_{CE} = 10\ \text{V}, T_A = -55^{\circ}\text{C}$	h_{FE4}	10	---	---

Small Signal Characteristics	Symbol	Min	Max	Unit
Magnitude of Common Emitter Small Signal Short Circuit Forward Current Transfer Ratio $V_{CE} = 10\ \text{V}, I_E = 2.0\ \text{mA}, f = 100\ \text{MHz}$	$ h_{fe} $	12	36	---
Collector to Base Feedback Capacitance $V_{CB} = 10\ \text{V}, I_E = 0, 100\ \text{kHz} < f < 1\ \text{MHz}$	C_{cb}	---	0.8	pF
Collector to Base Time Constant $V_{CB} = 10\ \text{V}, I_E = 2.0\ \text{mA}, f = 63.6\ \text{MHz}$	$r_b C_C$	1.0	8.0	ps
Common Emitter Small Signal Power Gain $V_{CE} = 10\ \text{V}, I_C = 2.0\ \text{mA}, f = 450\ \text{MHz}$	G_{PE}	17	25	dB